

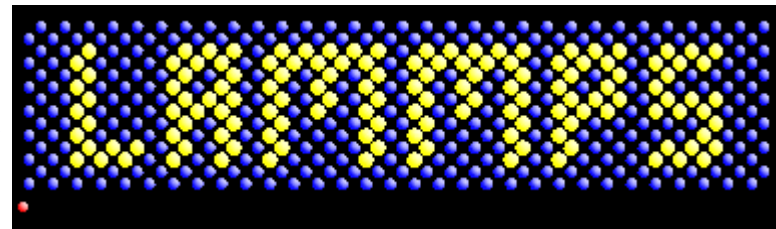
12月7日上机实习安排

LAMMPS软件中ReaxFF力场的使用:

1. 自行安装LAMMPS软件的Windows版本
2. Reactive mechanism investigation of nickel-catalyzed transformation of amorphous carbon (α -C) into graphene rapid thermal processing (RTP)

LAMMPS软件的简介

- LAMMPS: Large-scale Atomic/Molecular Massively Parallel Simulator
- 由美国能源部两个实验室发布(free and open-source)
- MD, MC → 从原子尺度到介观尺度
- CPU, GPU皆可, 可并行
- 易于扩展, eg: 添加力场方便
- 一个脚本可运行一个或多个模拟
- 非图形化界面
- 官网: <http://lammps.sandia.gov/>



LAMMPS输入文件

- 初试结构文件——data文件
- 模拟控制文件——in文件(input script)
 1. Initialization
 2. Atom definition
 3. Settings
 4. Run a simulation
- ✓ 每行命令中的不同字段由空格或者制表符分隔开来，每个字段可以由字母、数字、下划线、或标点符号构成；
- ✓ 每行命令中第一个字段表示命令名，之后的字段都是相关的参数； eg: `units lj/real/metal/si/cgs` `units metal`
- ✓ 注意：lammps里很多命令都有自己的默认设置，很多命令都是在需要修改默认值的情况下才特别设置的。

LAMMPS输入文件

- ✓ 每行后的“&”表示续行（类似fortran），“#”表示注释，\$是跟声明变量有关的；
- ✓ 每一非空行都被认为是一条命令（大小写敏感，极少有命令或参数大写的）；
- ✓ 读入一行执行一行，有些命令在其他命令后有效，有些命令要用到其他命令的输出；比如，要设定一组原子的温度，需要先用group命令定义哪些原子属于这个组才行；
- ✓ in文件中各命令的顺序可能会对计算产生影响，但大部分情况下不会有影响；

LAMMPS输出文件

- log.lammps文件——记录了整个计算过程屏幕上显示的所有信息
- dump文件——输出应力、能量、原子位置、速度等，由dump命令控制输出文件，eg: xyz文件
- restart文件——断点续算文件，由write_restart命令控制。

data文件实例

a-C@Ni

3 atoms

2 atom types

0 12.4592 xlo xhi

0 12.9480 ylo yhi

0 60.0000 zlo zhi

Masses

1 12.0107

2 58.6934

Atoms

1 1 0.0 7.366430000 11.931600000 29.905000000

2 2 0.0 0.202289000 12.728100000 11.926800000

3 2 0.0 10.202289000 22.728100000 20.926800000

in文件实例

a-C@Ni

1. Initialization

units real

#能量单位

newton on #turns Newton's 3rd law on or off for pairwise and bonded interactions

dimension 3

#模拟盒子的维度

boundary p p p

#盒子三个反向都是三维周期的

2. Atom definition

atom_style charge

#模拟中原子处理类型（带电荷的）

read_data data.Ni-C-600K-final

#读取结果文件

pair_style reax/c lmp_control

#用ReaxFF处理pairwise interaction

pair_coeff * *ffield.reax.FC C Ni

#不同元素pairwise的力场参数

3. Settings

neighbor 2.0 bin

#building of neighbor list 距离 算法

neigh_modify every 10 delay 0 check no #building and use of neighbor list

fix 1 all qeq/reax 1 0.0 10.0 1.0e-6 reax/c #Qeq方法处理电荷结合ReaxFF

in文件实例

4. Run a simulation with output (thermo & dump)

minimize 1.0e-12 1.0e-12 1000 1000

min_style cg

min_modify dxmax 0.2

} Geometry Optimization

timestep 0.25

run_style verlet

fix 2 all nvt temp 900 900 1.0

thermo 40

thermo_style custom time temp press pe ke etotal enthalpy

dump 1 all xyz 40 a-C-on-Ni-900K.xyz

run 60000

unfix 2

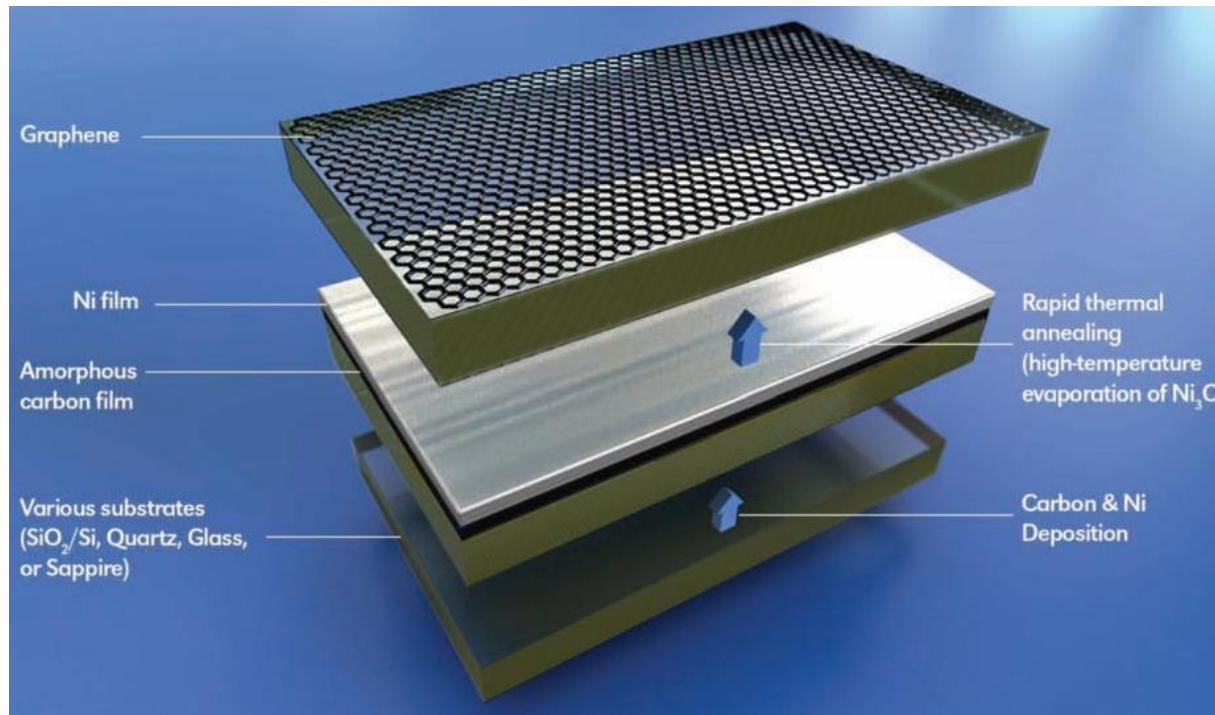
undump 1

} MD

Ab Initio Molecular Dynamics Simulations of Nickel-Catalyzed Transformation of Amorphous Carbon into Graphene in Rapid Thermal Processing

Graphene Growth in Rapid Thermal Processing (RTP)

➤ Ni evaporation at 1100° C much lower than the Ni evaporation point

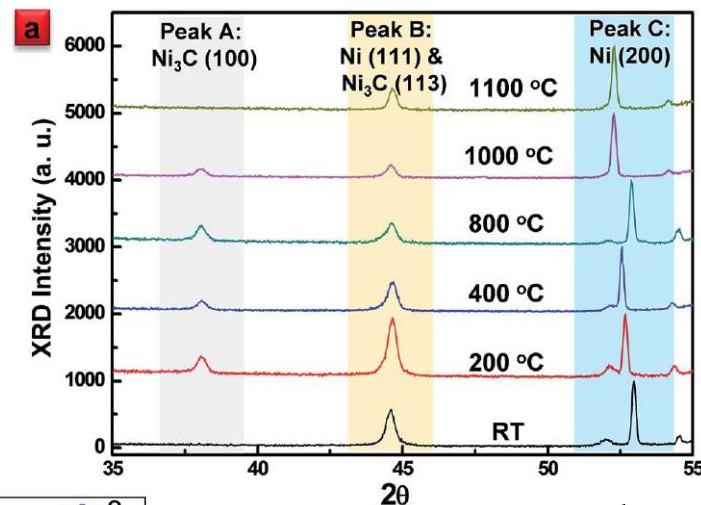
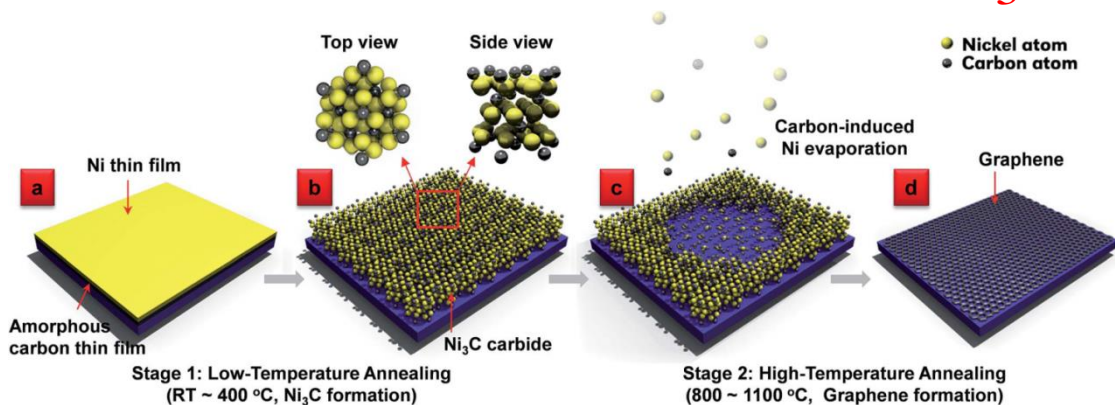


Compared to CVD:

- No post-growth Ni etching
- Transfer-free (directly grown on various dielectric surfaces)
- Control number of graphene layers

Graphene Growth in Rapid Thermal Processing (RTP)

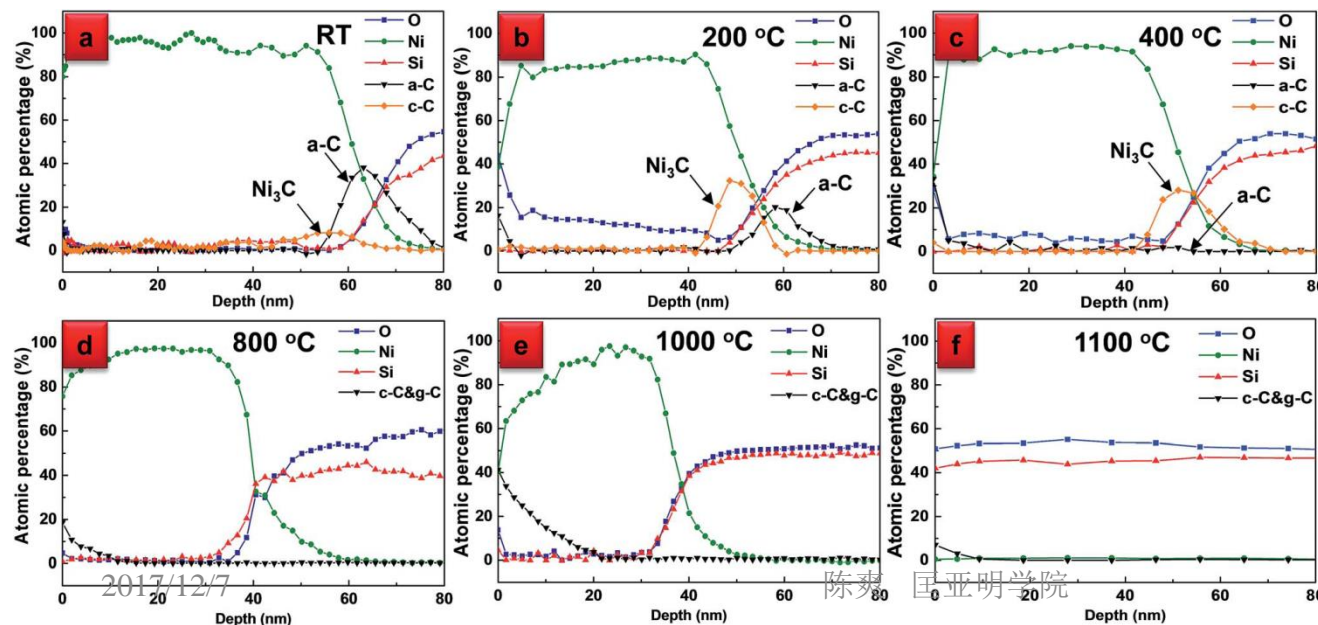
➤ Formation of metastable Ni_3C



Temperature-resolved
glancing-angle XRD

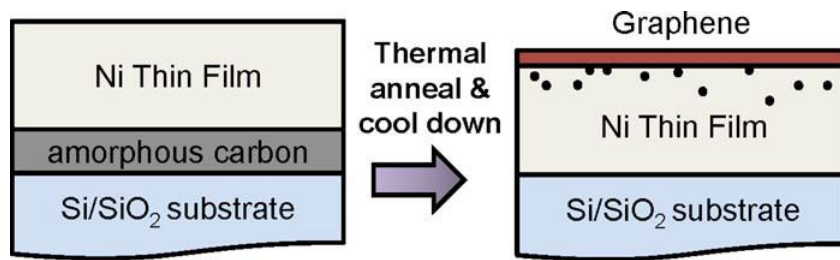
Temperature-resolved
AES

RSC Adv. **2015**, *5*, 99037-99043.



Heating and Cooling of *a*-C/Ni Bilayer

- Ni-catalyzed *a*-C → graphene (top layer)



Appl. Phys. Lett. **2010**, 96, 063110.

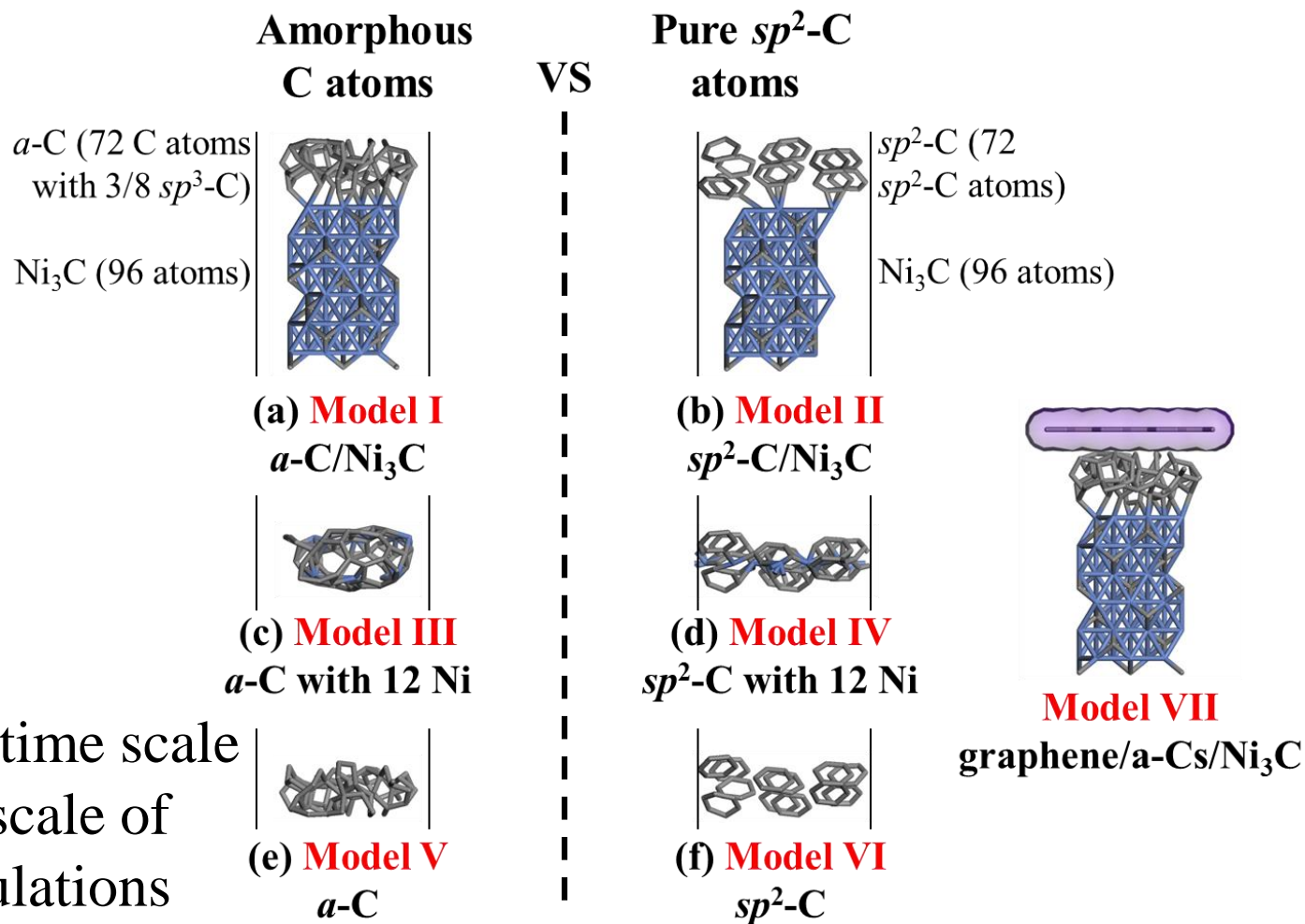
Appl. Phys. Lett. **2010**, 96, 153105.

- Graphitic C formation: 640–730° C
- Metal-induced crystallization and layer exchange mechanism (not a dissolution/precipitation mechanism)
- Reverse dissolution of graphitic C: > 950° C

C in Ni:

- Low concentration
- High transport rate

Design of AIMD Slab Models



Limited by time scale
and length scale of
AIMD simulations

Computational Details

- Simulation setting (AIMD simulations in CP2K)
 - *NVT* ensemble with **stepwise temperature (*T*) increasing: 300 K, 600 K, 900K, 1200 K, 1800 K**, (2400 K, and 3000 K)
 - Each temperature with **15-ps** AIMD running
 - PBE-D3 (dispersion cutoff radius: 20 Å)
 - Gaussian plane-wave (GPW) method: GTH pseudopotential (330 Ry) + DZP (33 Ry)
 - SCF: 10^{-6} a.u.
 - Time step: 1 fs
 - Nosé-Hoover chain thermostat

Final Snapshots (After 75 ps and 1800 K)

➤ Phase separation (C atoms can enter Ni_3C layer.)

➤ Localized dome-like patch vs relatively flat patch

➤ Carbon roll/shell vs flat patch

➤ Catalysis of Ni atoms

- Stabilize the dangling C atoms

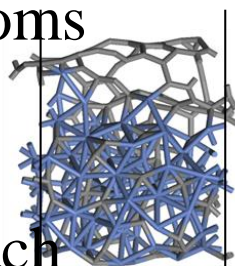
- Support newly-formed graphene

➤ Formations of Ni clusters

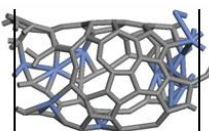
Amorphous
C atoms

VS

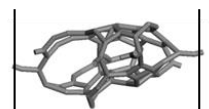
Pure sp^2 -C
atoms



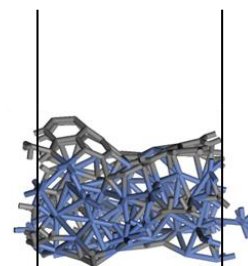
(a') **Model I**
 $a\text{-C}/\text{Ni}_3\text{C}$



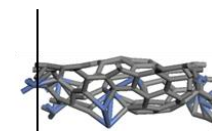
(c') **Model III**
 $a\text{-C}$ with 12 Ni



(e') **Model V**
 $a\text{-C}$



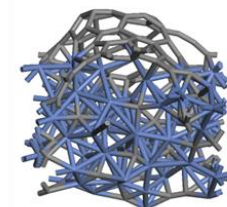
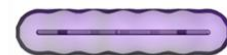
(b') **Model II**
 $sp^2\text{-C}/\text{Ni}_3\text{C}$



(d') **Model IV**
 $sp^2\text{-C}$ with 12 Ni



(f') **Model VI**
 $sp^2\text{-C}$



Model VII
graphene/ $a\text{-Cs}/\text{Ni}_3\text{C}$

模拟的实施

- Model building: amorphous C atoms@Ni(111) surface by MS
→ generate data file
- Step-by-step temperature increasing simulations with *NVT* ensemble: 300 K → ... → 3000 K
- Put data, in, ffield.reax.FC, and lmp_control files into
E:\Program Files\LAMMPS 64-bit 20170127\bin
- 运行cmd
- 往下输入命令:
- ✓ E:
- ✓ cd E:\Program Files\LAMMPS 64-bit 20170127\bin
- ✓ set OMP_NUM_THREADS=2
- ✓ lmp_mpi.exe < in file name
- xyz轨迹文件可用VMD软件读取